

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-150V	85mΩ@-10V	-30A
	94mΩ@-4.5V	



合肥矽普半导体

Siliup Semiconductor Technology Co., Ltd

技术 品质 服务

www.siliup.com

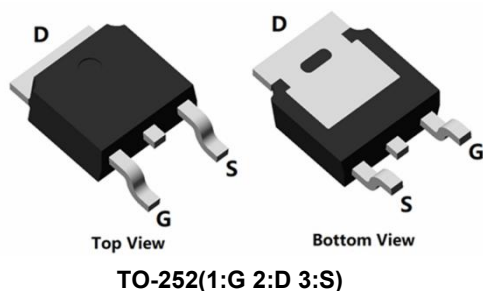
Feature

- Fast Switching
- Low Gate Charge and Rdson
- Advanced Split Gate Trench Technology
- 100% Single Pulse avalanche energy Test

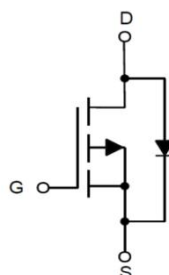
Applications

- Power switching application
- DC-DC Converter
- Power Management

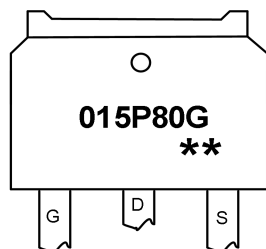
Package



Circuit diagram



Marking



015P80G : Product code
****** : Week code

Order Information

Device	Package	Unit/Tube
SP015P80GTH	TO-252	2500

Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	-150	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current (Tc=25°C)	I_D	-30	A
Continuous Drain Current (Tc=100°C)	I_D	-20	A
Pulsed Drain Current	I_{DM}	-120	A
Single Pulse Avalanche Energy ¹	E_{AS}	380	mJ
Power Dissipation (Tc=25°C)	P_D	130	W
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	0.96	°C/W
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C

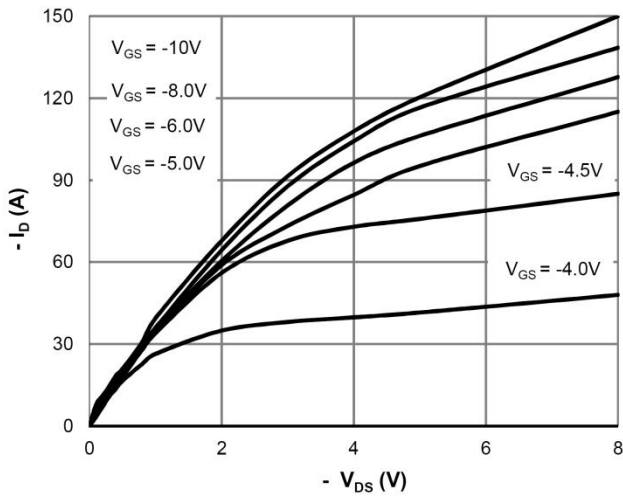
Electrical characteristics (Ta=25°C, unless otherwise noted)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V , ID= -250uA	-150	-	-	V
Drain Cut-Off Current	I _{DSS}	VDS= -120V , VGS=0V	-	-	-1	μA
Gate Leakage Current	I _{GSS}	VGS= ± 20V , VDS=0V	-	-	± 100	nA
Gate Threshold Voltage	V _{GS(th)}	VGS=VDS , ID = -250uA	-1	-1.9	-2.5	V
Drain-Source ON Resistance	R _{DS(ON)}	VGS= -10V , ID= -30A	-	85	106	mΩ
	R _{DS(ON)}	VGS= -4.5V , ID= -20A	-	94	125	
Dynamic Characteristics						
Input Capacitance	C _{iss}	VDS= -75V,VGS=0V,f=1MHZ	-	3275	-	pF
Output Capacitance	C _{oss}		-	137	-	
Reverse Transfer Capacitance	C _{rss}		-	14	-	
Total Gate Charge	Q _g	VDS= -75V , VGS= -10V , ID= -15A	-	92	-	nC
Gate-Source Charge	Q _{gs}		-	9	-	
Gate-Drain Charge	Q _{gd}		-	19	-	
Switching Characteristics						
Turn-On Delay Time	t _{d(on)}	VDD= -75V, VGS=-10V , RG=1.6Ω, ID= -15A	-	68	-	nS
Rise Time	t _r		-	18	-	
Turn-Off Delay Time	t _{d(off)}		-	70	-	
Fall Time	t _f		-	35	-	
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V _{SD}	I _S = -1A, VGS = 0V	-	-	-1.2	V
Maximum Body-Diode Continuous Current	I _S		-	-	-30	A
Reverse Recovery Time	T _{rr}	I _S = -15A, di/dt=100A/us, T _J =25℃	-	350	-	nS
Reverse Recovery Charge	Q _{rr}		-	86	-	nC

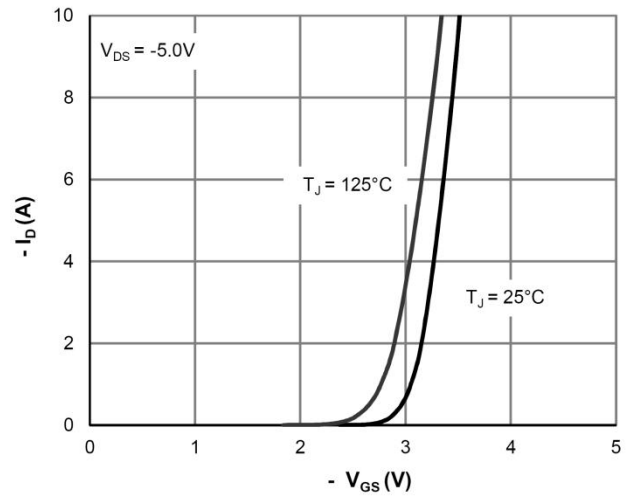
Note :

- The test condition is $V_{DD}=-50V, V_{GS}=-10V, L=0.5mH, R_G=25\Omega$

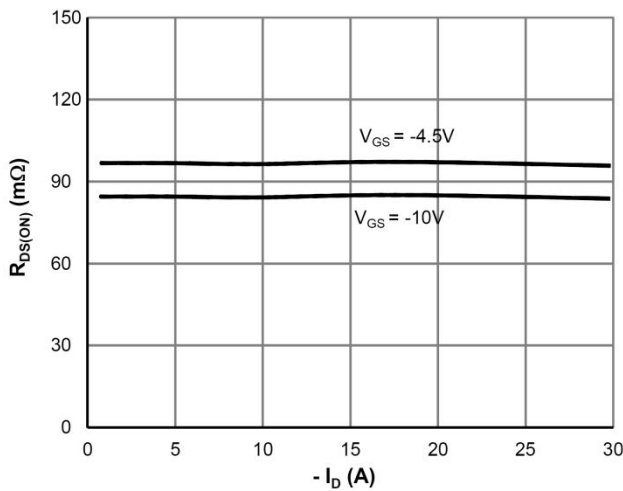
Typical Characteristics



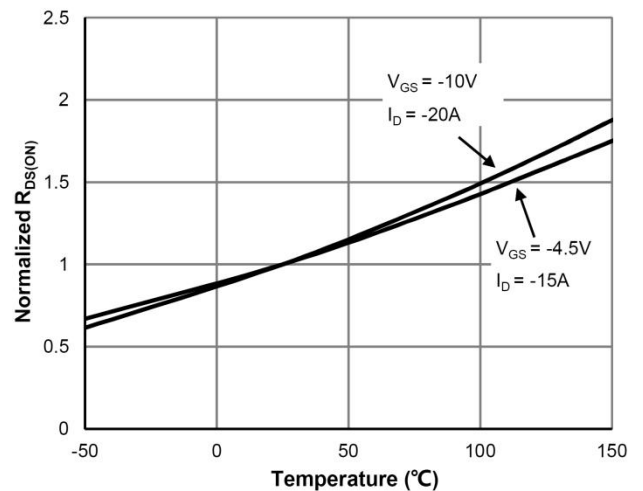
Saturation Characteristics



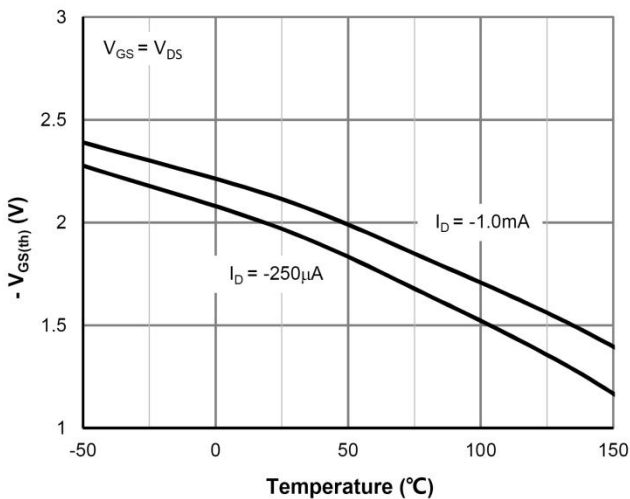
Transfer Characteristics



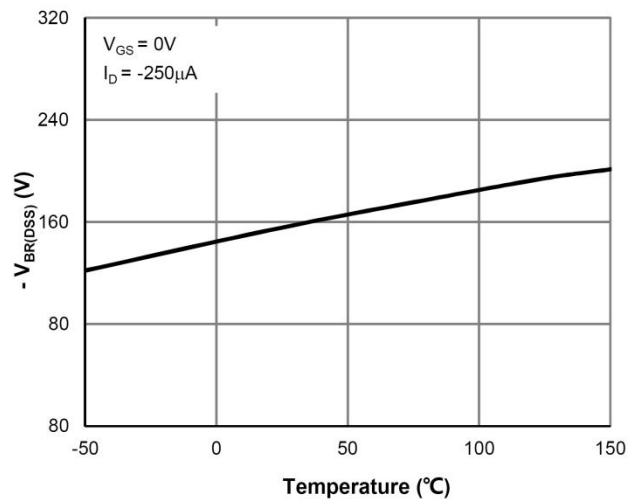
$R_{DS(ON)}$ vs. Drain Current



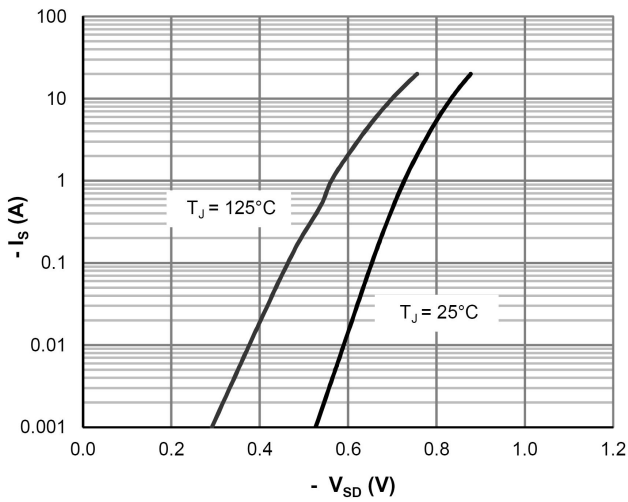
$R_{DS(ON)}$ vs. Junction Temperature



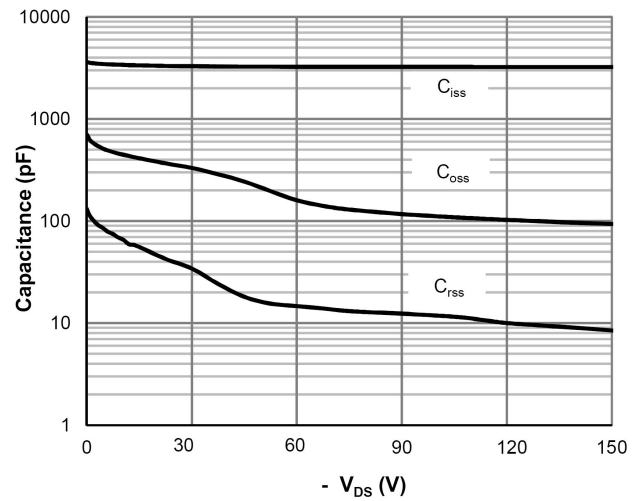
$V_{GS(th)}$ vs. Junction Temperature



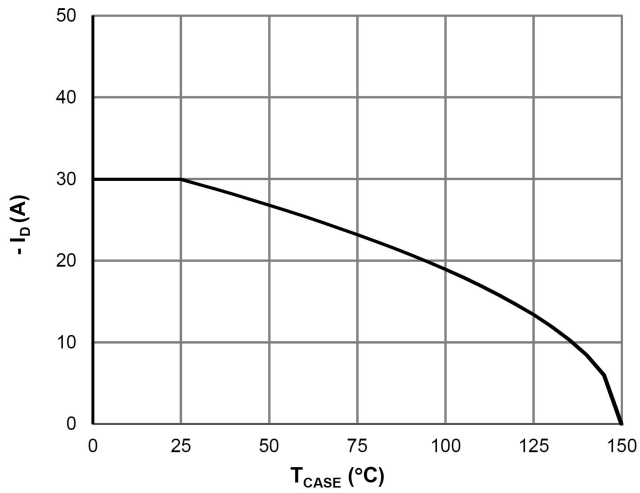
$V_{BR(DSS)}$ vs. Junction Temperature



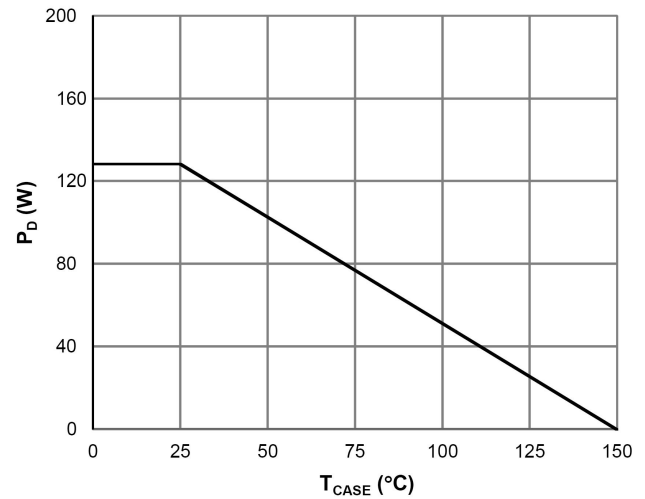
Body-Diode Characteristics



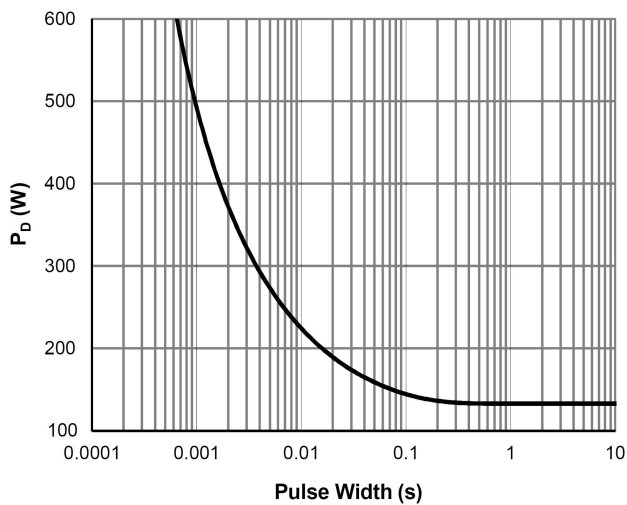
Capacitance Characteristics



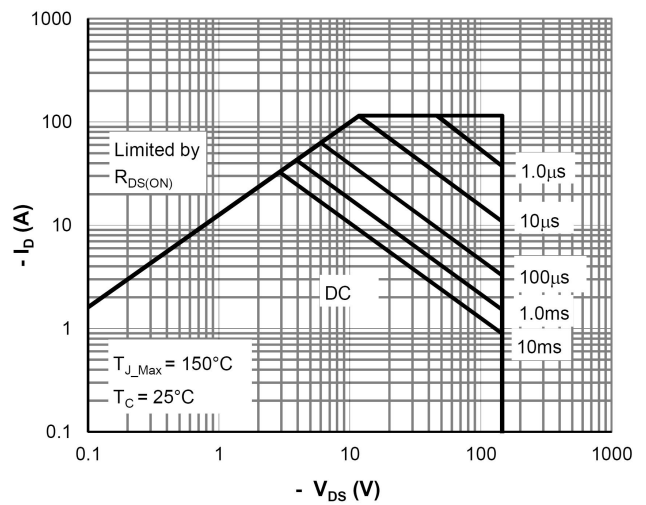
Current De-rating



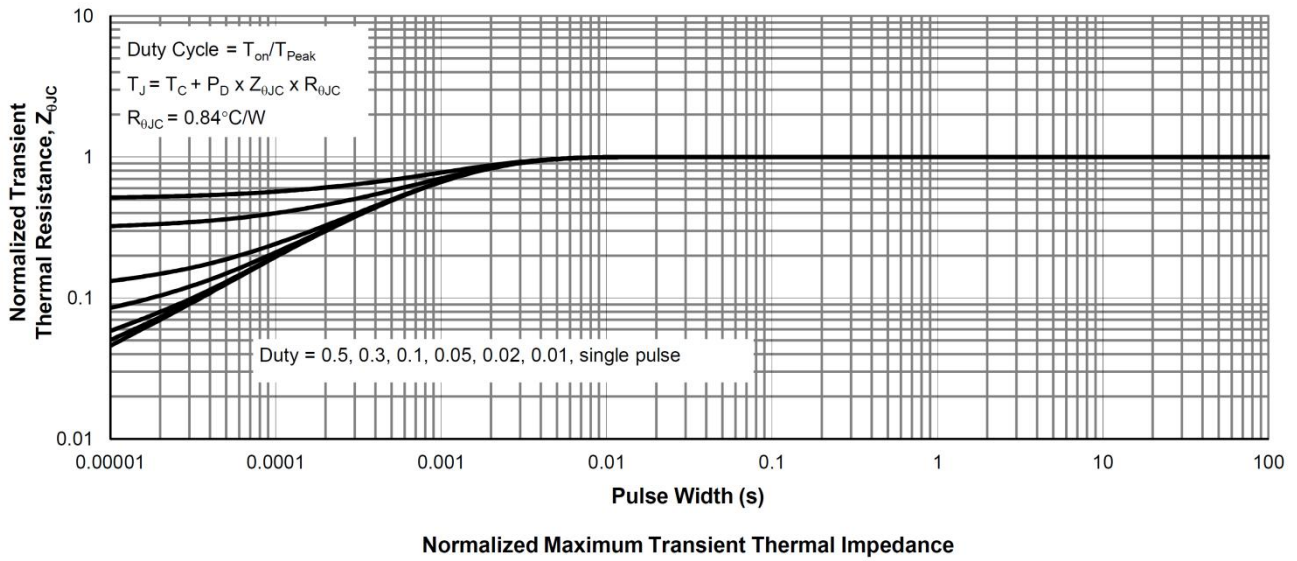
Power De-rating

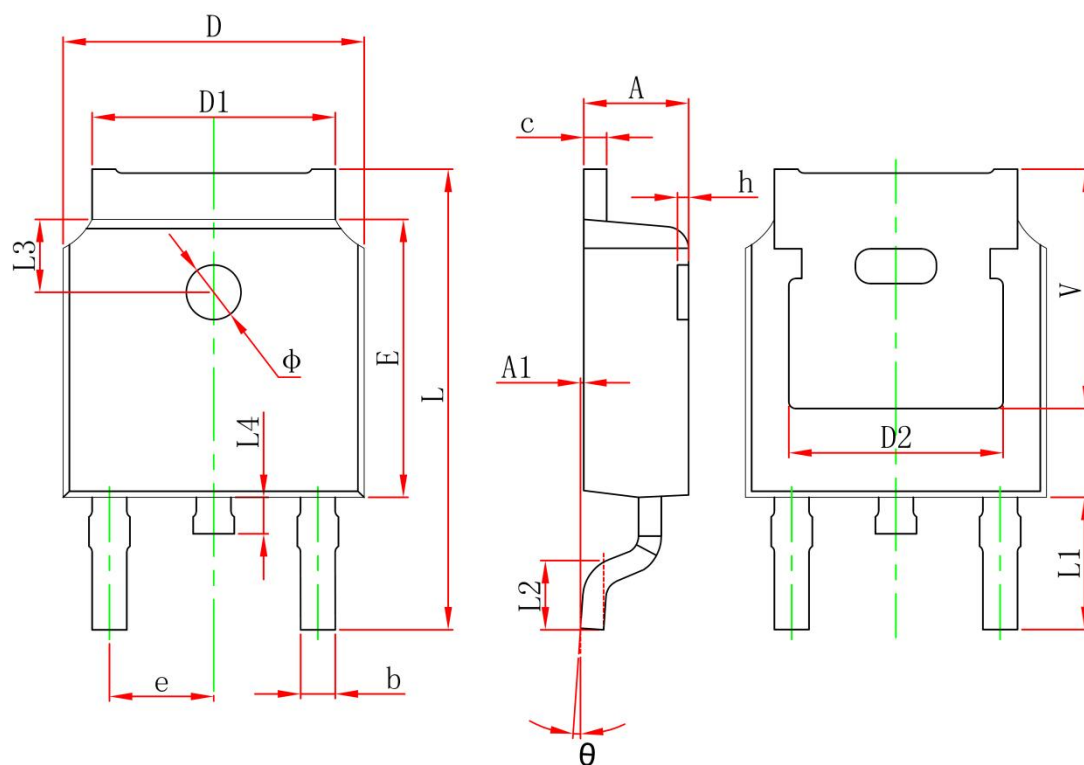


Single Pulse Power Rating, Junction-to-Case



Maximum Safe Operating Area



TO-252 Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
ϕ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 REF.		0.211 REF.	